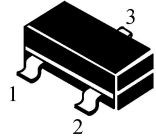




GMC3356

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



■FEATURES 特點

NPN High Frequency Transistor

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Collector-Emitter Voltage 集電極發射極電壓	V_{CEO}	12	Vdc
Collector-Base Voltage 集電極基極電壓	V_{CBO}	20	Vdc
Emitter-Base Voltage 發射極基極電壓	V_{EBO}	3.0	Vdc
Collector Current-Continuous 集電極電流-連續	I_c	100	mAdc

■THERMAL CHARACTERISTICS 熱特性

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Total Device Dissipation 總耗散功率 FR-5 Board(1) $T_A=25^{\circ}\text{C}$ 環境溫度為 25°C Derate above 25°C 超過 25°C 遞減	P_D	225 1.8	mW mW/ $^{\circ}\text{C}$
Total Device Dissipation 總耗散功率 Alumina Substrate 氧化鋁襯底,(2) $T_A=25^{\circ}\text{C}$ Derate above 25°C 超過 25°C 遞減	P_D	300 2.4	mW mW/ $^{\circ}\text{C}$
Thermal Resistance Junction to Ambient 熱阻	$R_{\theta JA}$	417	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 結溫和儲存溫度	T_J, T_{stg}	-55to+150 $^{\circ}\text{C}$	

GMC3356

■DEVICE MARKING 打標

GMC3356(2SC3356)=R25
H_{FE}:50-100; 80-150; 120-220; 200-300

■ELECTRICAL CHARACTERISTICS 電特性

(T_A=25°C unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Emitter Cutoff Current 發射極截止電流(V _{EB} =1.0v,I _C =0)	I _{EBO}	—	—	1.0	μA
Collector Cutoff Current 集電極截止電流(V _{CB} =10v,I _E =0)	I _{CBO}	—	—	1.0	μA
Collector-Base Breakdown Voltage 集電極基極擊穿電壓(I _C =10uA)	V _{(BR)CBO}	20	—	—	V
Collector-Emitter Breakdown Voltage 集電極發射極擊穿電壓(I _C =1mA)	V _{(BR)CEO}	12	—	—	V
Emitter-Base Breakdown Voltage 發射極基極擊穿電壓(I _E =10uA)	V _{(BR)EBO}	3	—	—	V
DC Current Gain 直流電流增益 (V _{CE} =10v,I _C =20mA)	H _{FE}	50	—	300	
Gain Bandwidth Product 增益帶寬乘積(V _{CE} =10v,I _C =20mA)	f _T	—	7000	—	MHz
Noise Figure 噪声係數 (V _{CE} =10V,I _C =7mA,f=1.0GHz)	NF	—	—	2.0	dB
Feed-Back Capacitance 反饋電容 (V _{CB} =10v,I _E =0,f=1.0MHz)	C _{re}	—	0.55	1.0	pF

1. FR-5=1.0×0.75×0.062in.
2. Alumina=0.4×0.3×0.024in.99.5%alumina.